National Semiconductor

February 1988

CD40106BM/CD40106BC Hex Schmitt Trigger

General Description

The CD40106B Hex Schmitt Trigger is a monolithic complementary MOS (CMOS) integrated circuit constructed with N and P-channel enhancement transistors. The positive and negative-going threshold voltages, V_{T+} and V_{T-}, show low variation with respect to temperature (typ 0.0005V/°C at $V_{DD} = 10V$), and hysteresis, $V_{T+} - V_{T-} \geq 0.2\ V_{DD}$ is guaranteed.

All inputs are protected from damage due to static discharge by diode clamps to V_{DD} and V_{SS}.

Features

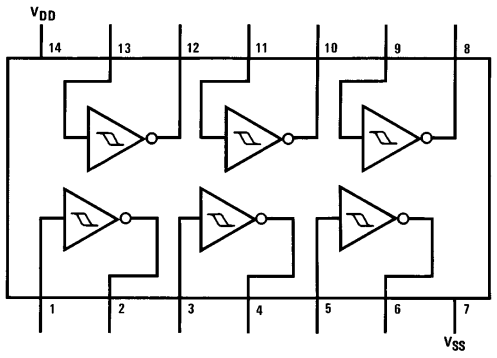
■ Wide supply voltage range	3V to 15V
■ High noise immunity	0.7 V_{DD} (typ.)
■ Low power TTL compatibility	Fan out of 2 driving 74L or 1 driving 74LS
■ Hysteresis	0.4 V_{DD} (typ.) 0.2 V_{DD} guaranteed

■ Equivalent to MM54C14/MM74C14

■ Equivalent to MC14584B

Connection Diagram

Dual-In-Line Package



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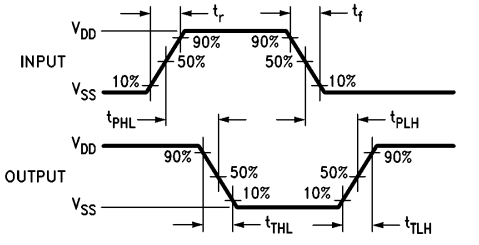
Top View

Switching Time Waveforms



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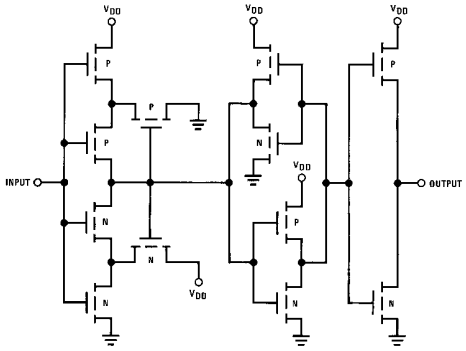
$t_r = t_f = 20$ ns

Order Number CD40106B

Schematic Diagram



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RRD-B30M105/Printed in U. S. A.

Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

DC Supply Voltage (V_{DD})	-0.5 to $+18$ V_{DC}
Input Voltage (V_{IN})	-0.5 to V_{DD} $+0.5$ V_{DC}
Storage Temperature Range (T_S)	$-65°C$ to $+150°C$
Power Dissipation (P_D)	
Dual-In-Line	700 mW
Small Outline	500 mW
Lead Temperature (T_L)	
(Soldering, 10 seconds)	260°C

Recommended Operating Conditions (Note 2)

DC Supply Voltage (V_{DD})	3 to 15 V_{DC}
Input Voltage (V_{IN})	0 to V_{DD} V_{DC}
Operating Temperature Range (T_A)	
CD40106BM	$-55°C$ to $+125°C$
CD40106BC	$-40°C$ to $+85°C$

DC Electrical Characteristics CD40106BM (Note 2)

Symbol	Parameter	Conditions	$-55°C$		$+25°C$			$+125°C$		Units
			Min	Max	Min	Typ	Max	Min	Max	
I_{DD}	Quiescent Device Current	$V_{DD} = 5V$, $V_{IN} = V_{DD}$ or V_{SS}		1.0			1.0		30	μA
		$V_{DD} = 10V$, $V_{IN} = V_{DD}$ or V_{SS}		2.0			2.0		60	μA
		$V_{DD} = 15V$, $V_{IN} = V_{DD}$ or V_{SS}		4.0			4.0		120	μA
V_{OL}	Low Level Output Voltage	$\|I_O\| < 1\ \mu A$								
		$V_{DD} = 5V$		0.05			0.05		0.05	V
		$V_{DD} = 10V$		0.05			0.05		0.05	V
		$V_{DD} = 15V$		0.05			0.05		0.05	V
V_{OH}	High Level Output Voltage	$\|I_O\| < 1\ \mu A$								
		$V_{DD} = 5V$	4.95		4.95	5		4.95		V
		$V_{DD} = 10V$	9.95		9.95	10		0.95		V
		$V_{DD} = 15V$	14.95		14.95	15		14.95		V
V_{T-}	Negative-Going Threshold Voltage	$V_{DD} = 5V$, $V_O = 4.5V$	0.7	2.0	0.7	1.4	2.0	0.7	2.0	V
		$V_{DD} = 10V$, $V_O = 9V$	1.4	4.0	1.4	3.2	4.0	1.4	4.0	V
		$V_{DD} = 15V$, $V_O = 13.5V$	2.1	6.0	2.1	5.0	6.0	2.1	6.0	V
V_{T+}	Positive-Going Threshold Voltage	$V_{DD} = 5V$, $V_O = 0.5V$	3.0	4.3	3.0	3.6	4.3	3.0	4.3	V
		$V_{DD} = 10V$, $V_O = 1V$	6.0	8.6	6.0	6.8	8.6	6.0	8.6	V
		$V_{DD} = 15V$, $V_O = 1.5V$	9.0	12.9	9.0	10.0	12.9	9.0	12.9	V
V_H	Hysteresis ($V_{T+} - V_{T-}$)	$V_{DD} = 5V$	1.0	3.6	1.0	2.2	3.6	1.0	3.6	V
		$V_{DD} = 10V$	2.0	7.2	2.0	3.6	7.2	2.0	7.2	V
		$V_{DD} = 15V$	3.0	10.8	3.0	5.0	10.8	3.0	10.8	V
I_{OL}	Low Level Output Current (Note 3)	$V_{DD} = 5V$, $V_O = 0.4V$	0.64		0.51	0.88		0.36		mA
		$V_{DD} = 10V$, $V_O = 0.5V$	1.6		1.3	2.25		0.9		mA
		$V_{DD} = 15V$, $V_O = 1.5V$	4.2		3.4	8.8		2.4		mA
I_{OH}	High Level Output Current (Note 3)	$V_{DD} = 5V$, $V_O = 4.6V$	-0.64		-0.51	-0.88		-0.36		mA
		$V_{DD} = 10V$, $V_O = 9.5V$	-1.6		-1.3	-2.25		-0.9		mA
		$V_{DD} = 15V$, $V_O = 13.5V$	-4.2		-3.4	-8.8		-2.4		mA
I_{IN}	Input Current	$V_{DD} = 15V$, $V_{IN} = 0V$		-0.10		-10^{-5}	-0.10		-1.0	μA
		$V_{DD} = 15V$, $V_{IN} = 15V$		0.10		10^{-5}	0.10		1.0	μA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Recommended Operating Conditions" and "Electrical Characteristics" provides conditions for actual device operation.

Note 2: $V_{SS} = 0V$ unless otherwise specified.

Note 3: I_{OH} and I_{OL} are tested one output at a time.

DC Electrical Characteristics CD40106BC (Note 2)

Symbol	Parameter	Conditions	−40°C		+25°C			+85°C		Units
			Min	Max	Min	Typ	Max	Min	Max	
I_{DD}	Quiescent Device Current	$V_{DD} = 5V$		4.0			4.0		30	μA
		$V_{DD} = 10V$		8.0			8.0		60	μA
		$V_{DD} = 15V$		16.0			16.0		120	μA
V_{OL}	Low Level Output Voltage	$\|I_O\| < 1\ \mu A$								
		$V_{DD} = 5V$		0.05			0.05		0.05	V
		$V_{DD} = 10V$		0.05			0.05		0.05	V
		$V_{DD} = 15V$		0.05			0.05		0.05	V
V_{OH}	High Level Output Voltage	$\|I_O\| < 1\ \mu A$								
		$V_{DD} = 5V$	4.95		4.95	5		4.95		V
		$V_{DD} = 10V$	9.95		9.95	10		0.95		V
		$V_{DD} = 15V$	14.95		14.95	15		14.95		V
V_{T-}	Negative-Going Threshold Voltage	$V_{DD} = 5V, V_O = 4.5V$	0.7	2.0	0.7	1.4	2.0	0.7	2.0	V
		$V_{DD} = 10V, V_O = 9V$	1.4	4.0	1.4	3.2	4.0	1.4	4.0	V
		$V_{DD} = 15V, V_O = 13.5V$	2.1	6.0	2.1	5.0	6.0	2.1	6.0	V
V_{T+}	Positive-Going Threshold Voltage	$V_{DD} = 5V, V_O = 0.5V$	3.0	4.3	3.0	3.6	4.3	3.0	4.3	V
		$V_{DD} = 10V, V_O = 1V$	6.0	8.6	6.0	6.8	8.6	6.0	8.6	V
		$V_{DD} = 15V, V_O = 1.5V$	9.0	12.9	9.0	10.0	12.9	9.0	12.9	V
V_H	Hysteresis ($V_{T+} - V_{T-}$) Voltage	$V_{DD} = 5V$	1.0	3.6	1.0	2.2	3.6	1.0	3.6	V
		$V_{DD} = 10V$	2.0	7.2	2.0	3.6	7.2	2.0	7.2	V
		$V_{DD} = 15V$	3.0	10.8	3.0	5.0	10.8	3.0	10.8	V
I_{OL}	Low Level Output Current (Note 3)	$V_{DD} = 5V, V_O = 0.4V$	0.52		0.44	0.88		0.36		mA
		$V_{DD} = 10V, V_O = 0.5V$	1.3		1.1	2.25		0.9		mA
		$V_{DD} = 15V, V_O = 1.5V$	3.6		3.0	8.8		2.4		mA
I_{OH}	High Level Output Current (Note 3)	$V_{DD} = 5V, V_O = 4.6V$	−0.52		−0.44	−0.88		−0.36		mA
		$V_{DD} = 10V, V_O = 9.5V$	−1.3		−1.1	−2.25		−0.9		mA
		$V_{DD} = 15V, V_O = 13.5V$	−3.6		−3.0	−8.8		−2.4		mA
I_{IN}	Input Current	$V_{DD} = 15V, V_{IN} = 0V$		−0.30		-10^{-5}	−0.30		−1.0	μA
		$V_{DD} = 15V, V_{IN} = 15V$		0.30		10^{-5}	0.30		1.0	μA

AC Electrical Characteristics*

$T_A = 25°C$, $C_L = 50$ pF, $R_L = 200k$, t_r and $t_f = 20$ ns, unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Units
t_{PHL} or t_{PLH}	Propagation Delay Time from Input to Output	$V_{DD} = 5V$		220	400	ns
		$V_{DD} = 10V$		80	200	ns
		$V_{DD} = 15V$		70	160	ns
t_{THL} or t_{TLH}	Transition Time	$V_{DD} = 5V$		100	200	ns
		$V_{DD} = 10V$		50	100	ns
		$V_{DD} = 15V$		40	80	ns
C_{IN}	Average Input Capacitance	Any Input		5	7.5	pF
C_{PD}	Power Dissipation Capacity	Any Gate (Note 4)		14		pF

*AC Parameters are guaranteed by DC correlated testing.

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed; they are not meant to imply that the devices should be operated at these limits. The table of "Recommended Operating Conditions" and "Electrical Characteristics" provides conditions for actual device operation.

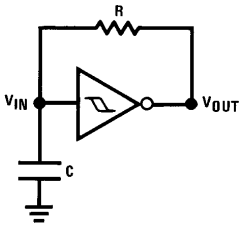
Note 2: $V_{SS} = 0V$ unless otherwise specified.

Note 3: I_{OH} and I_{OL} are tested one output at a time.

Note 4: C_{PD} determines the no load ac power consumption of any CMOS device. For complete explanation see 54C/74C Family Characteristics Application Note, AN-90.

Typical Applications

Low Power Oscillator



$$t_1 \approx RC \ell n \frac{V_{T+}}{V_{T-}}$$

$$t_2 \approx RC \ell n \frac{V_{DD} - V_{T-}}{V_{DD} - V_{T+}}$$

$$f \approx \frac{1}{RC \ell n \frac{V_{T+}(V_{DD} - V_{T-})}{V_{T-}(V_{DD} - V_{T+})}}$$

Note: The equations assume

$t_1 + t_2 >> t_{PHL} + t_{PLH}$

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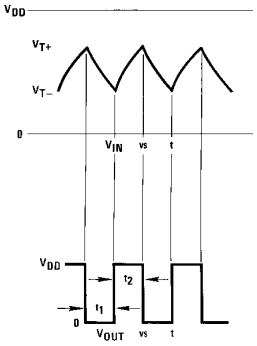

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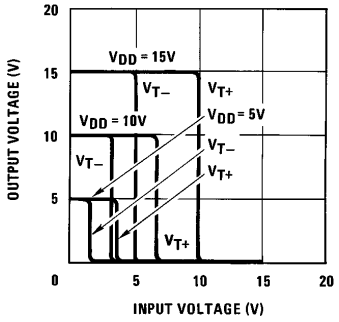
Typical Performance Characteristics

Typical Transfer Characteristics



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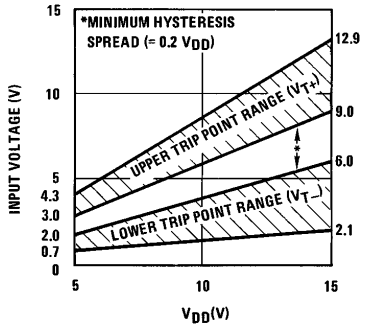
Guaranteed Trip Point Range



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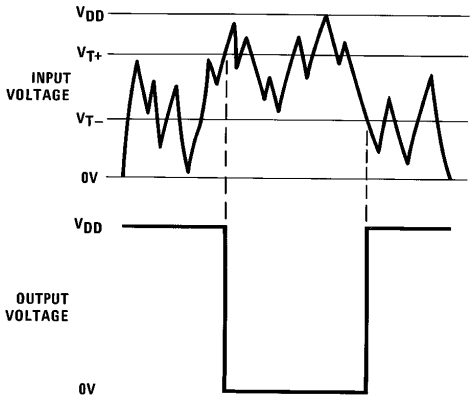

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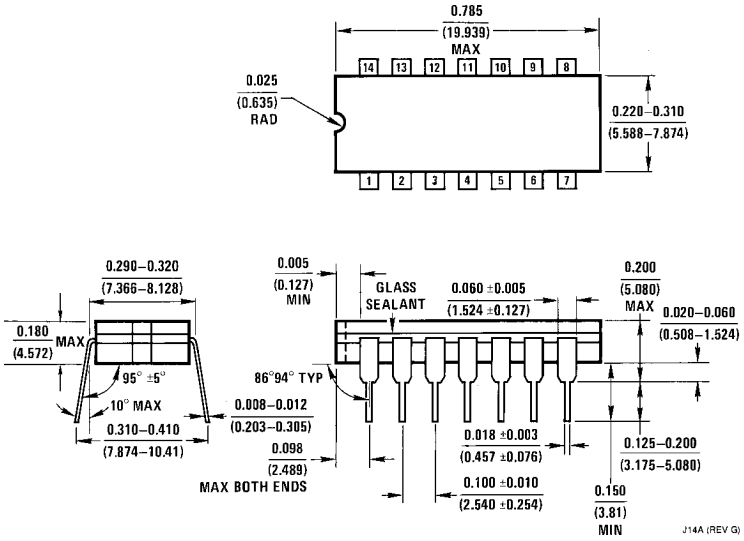
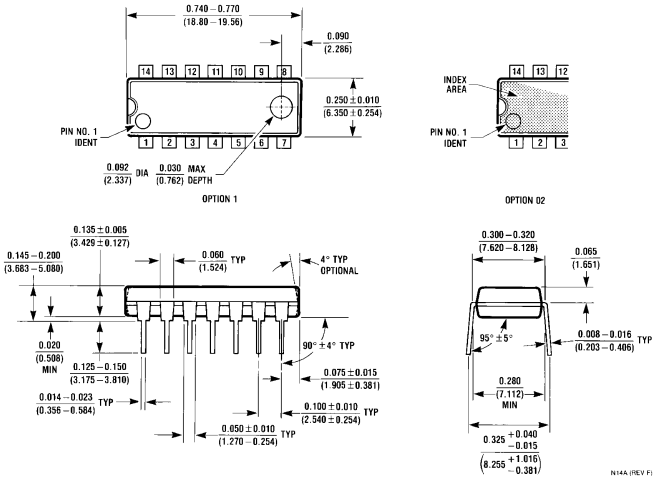
Physical Dimensions inches (millimeters)



Ceramic Dual-In-Line Package (J)
Order Number CD40106BMJ or CD40106BCJ
NS Package Number J14A

Physical Dimensions inches (millimeters) (Continued)



Molded Dual-In-Line Package (N)
Order Number CD40106BMN or CD40106BCN
NS Package Number N14A

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